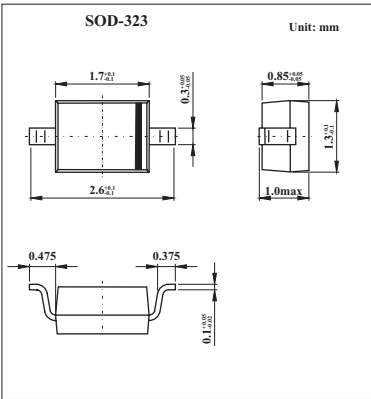


Silicon Epitaxial Planar Diode

1SV276

■ Features

- High Capacitance Ratio:C1V/C4V = 2.0(Typ.)
- Low Series Resistance:rs = 0.22 Ω (Typ.)



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse Voltage	VR	10	V
Junction Temperature	Tj	125	℃
Storage Temperature Range	Tstg	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	VR	IR = 1 μ A	10			V
Reverse Current	IR	VR = 10 V			3	nA
Capacitance	C1V	f = 1 MHz;VR = 1 V	15	16	17	pF
	C4V	f = 1 MHz;VR = 4 V	7	8	8.5	
Capacitance Ratio	C1V/C4V		1.8	2.0		
Series Resistance	rs	VR = 1V, f = 470 MHz		0.22	0.4	Ω

■ Marking

Marking	TL
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